

BCE108 Datasheet, Equivalent, Cross Reference Search

Type Designator: BCE108

Material of Transistor: Si

Polarity: NPN

Maximum Collector Power Dissipation (P_c): 0.15 W

Maximum Collector-Base Voltage $|V_{cb}|$: 30 V

Maximum Collector-Emitter Voltage $|V_{ce}|$: 20 V

Maximum Emitter-Base Voltage $|V_{eb}|$: 5 V

Maximum Collector Current $|I_c \text{ max}|$: 0.1 A

Max. Operating Junction Temperature (T_j): 125 °C

Transition Frequency (f_t): 200 MHz

Collector Capacitance (C_c): 6 pF

Forward Current Transfer Ratio (h_{FE}), MIN: 180

Noise Figure, dB: -

Package: SOT23